## **Ingrid Koslow**

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/11385332/publications.pdf

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		1478505	1588992	
8	195	6	8	
papers	citations	h-index	g-index	
8	8	8	249	
all docs	docs citations	times ranked	citing authors	

#	Article	IF	CITATIONS
1	30-mW-Class High-Power and High-Efficiency Blue Semipolar (10ar1ar1) InGaN/GaN Light-Emitting Diodes Obtained by Backside Roughening Technique. Applied Physics Express, 2010, 3, 102101.	2.4	77
2	Quantum-confined Stark effect on photoluminescence and electroluminescence characteristics of InGaN-based light-emitting diodes. Journal Physics D: Applied Physics, 2008, 41, 165105.	2.8	55
3	Vertical Stand Transparent Light-Emitting Diode Architecture for High-Efficiency and High-Power Light-Emitting Diodes. Japanese Journal of Applied Physics, 2010, 49, 080210.	1.5	20
4	Optimization of Device Structures for Bright Blue Semipolar (1011) Light Emitting Diodes via Metalorganic Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2010, 49, 070206.	1.5	19
5	Semipolar Single-Crystal ZnO Films Deposited by Low-Temperature Aqueous Solution Phase Epitaxy on GaN Light-Emitting Diodes. Applied Physics Express, 2011, 4, 126502.	2.4	11
6	Determination of polarization fields in group III-nitride heterostructures by capacitance-voltage-measurements. Journal of Applied Physics, 2016, 119, .	2.5	9
7	Precise determination of polarization fields in c-plane GaN/Al x Ga1-x N/GaN heterostructures with capacitance–voltage-measurements. Japanese Journal of Applied Physics, 2019, 58, SCCB08.	1.5	3
8	Customized Filter Cube in Fluorescence Microscope Measurements of InGaN/GaN Quantum-Well Characterization. Japanese Journal of Applied Physics, 2009, 48, 098003.	1.5	1